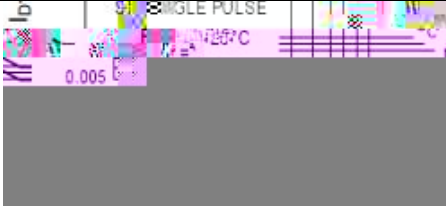
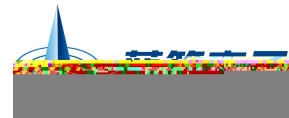


/ Revised record

A	2020.07.22		2N7002BKMB		
B	2021-8-16	4	DFN1006-3L-0.5 DFN1006-3L		
C	2022-5-13	2			

**/ Descriptions**

DFN1006-3L N MOS

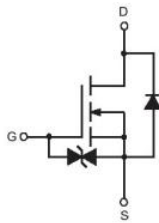
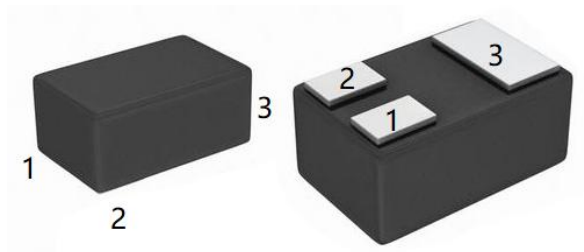
N-Channel Enhancement Mode Field Effect Transistor in a DFN1006-3L Plastic Package.

/ Features**2KV**

Sensitive gate trigger current and Low Holding current.ESD protected up to 2KV.HF Product.

/ Applications

Intended for use in general purpose switching and phase control applications.

/ Equivalent Circuit**/ Pinning**

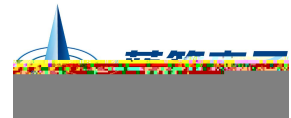
Pin1:G

Pin2:S

Pin3:D

/ Marking

See Marking Instructions.



Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage	V_{DGR}	60	V
Drain Current - Continuous	$I_D (T_a=25^{\circ}\text{C})$	300	mA
	$I_D (T_a=85^{\circ}\text{C})$	210	
Drain Current - Pulsed Gate-	I_{DM}	1200	mA

/ Electrical Characteristic Curve

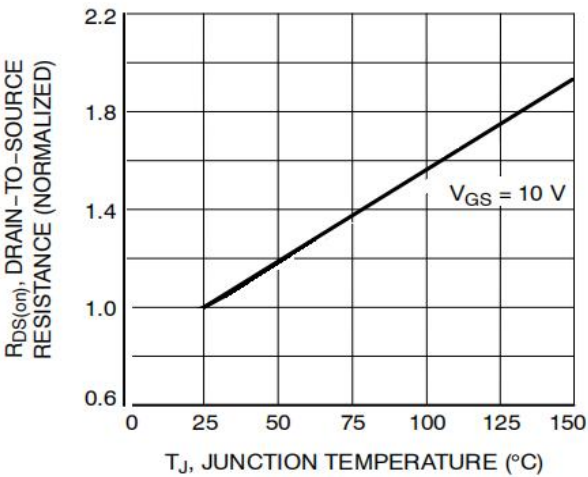
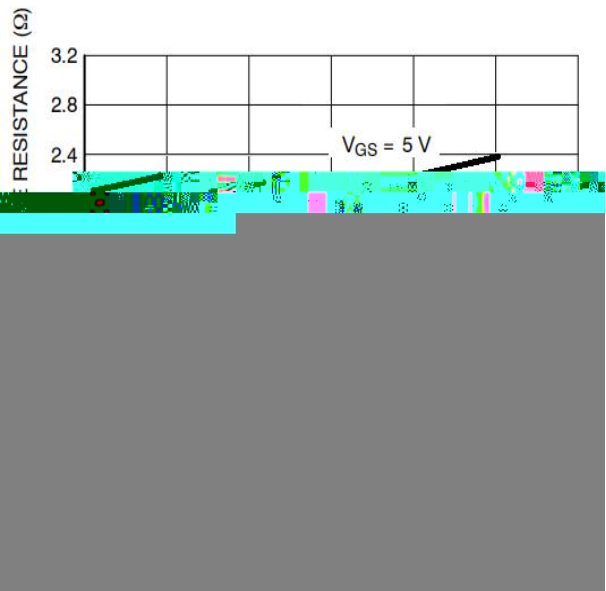
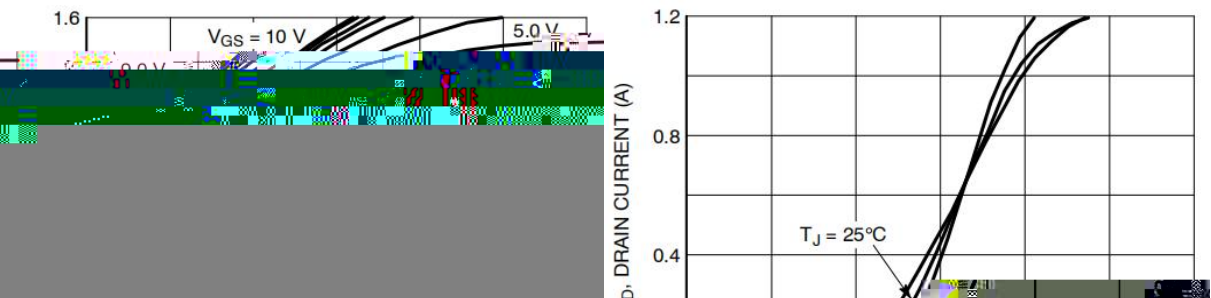
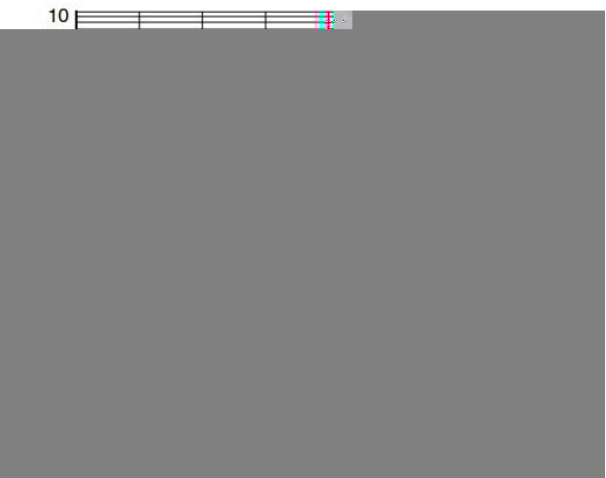
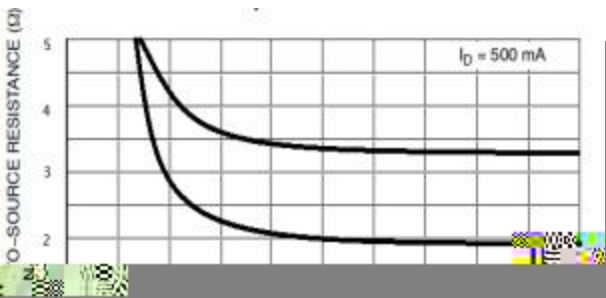


Figure 4 On-Resistance Variation with Temperature



/ Electrical Characteristic Curve

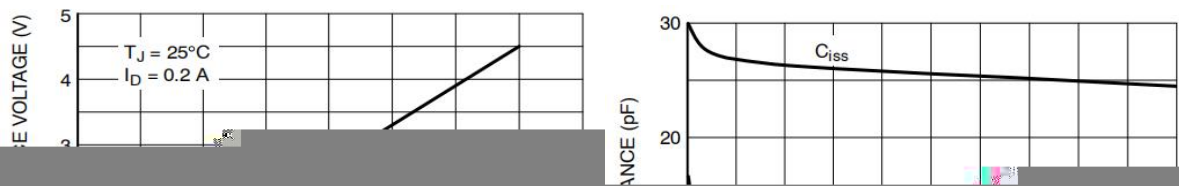
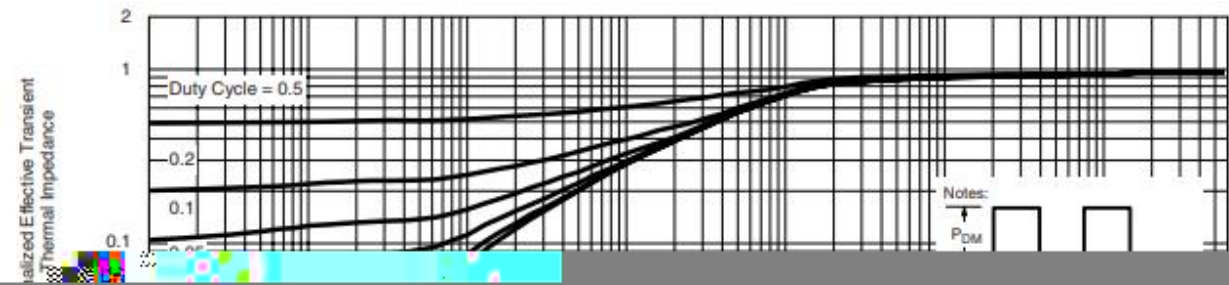
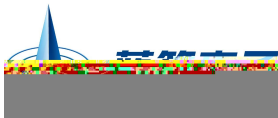
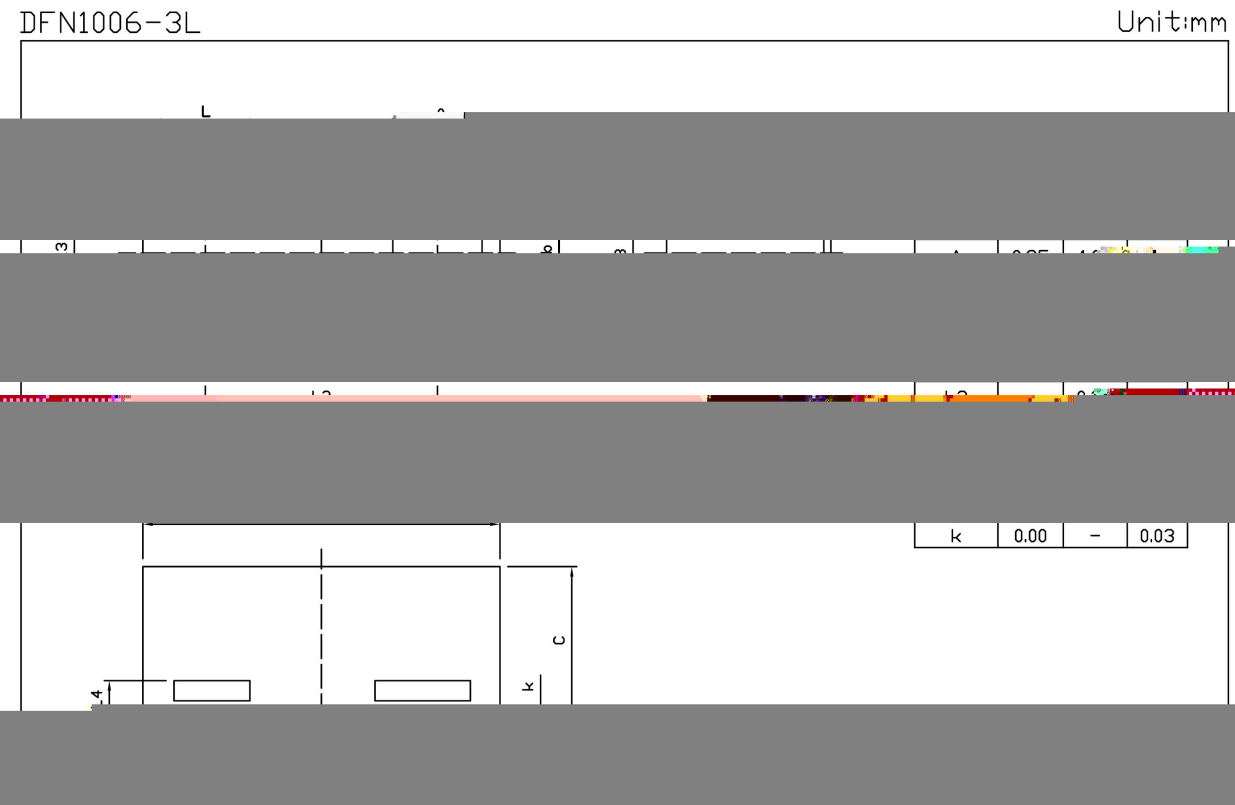


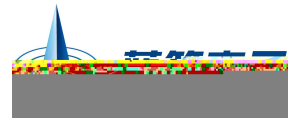
Figure 9 : Safe Operation Area





/ Package Dimensions





/ Marking Instructions

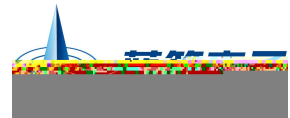


说明：

702K2： 为型号代码

Note:

702K2: Product Type



() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- | | | | | | |
|---|-------|-----|-----------|--------|--|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180°C, Time:60~90sec. |
| 2 | 245±5 | | 5±0.5sec; | | 2.Peak Temp.:245±5°C, Duration:5±0.5sec. |
| 3 | | 2 | 10°C/sec. | | 3. Cooling Speed: 2~10°C/sec. |

/ Resistance to Soldering Heat Test Conditions

260±5°C	10±1 sec.	Temp.:260±5	Time:10±1 sec
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/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱